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Smith

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Shiro SAKAI
Serial No.: 10/056,611
Filed : January 24, 2002
Title : METHOD FOR MANUFACTURING GALLIUM NITRIDE COMPOUND
SEMICONDUCTOR ELEMENT AND GALLIUM NITRIDE COMPOUND
SEMICONDUCTOR ELEMENT

Art Unit : 2813
Examiner : Thanh T. NGUYEN

Assistant Commissioner for Patents
Washington, DC 20231

REPLY UNDER 37 CFR § 1.111

In response to the Office Action dated October 7, 2002, please amend the application as follows and consider the included remarks.

IN THE TITLE:

In accordance with the Examiner's suggestion, please replace the title with the following.

--METHOD FOR MANUFACTURING GALLIUM NITRIDE COMPOUND
SEMICONDUCTOR ELEMENT--

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IN THE CLAIMS:

Please cancel claims 1 and 2 without prejudice or disclaimer and amend claims 3-9 as follows. Also, please add new claim 15. Marked-up versions of the amended claims are attached.

SUB B-7
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3. (Amended) A method for manufacturing a GaN compound semiconductor element, comprising the steps of:
- (a) forming, on a substrate, an N type GaN compound semiconductor layer and a